



# **30V, N-Channel NexFET™ Power MOSFETs**

Check for Samples: CSD17522Q5A

#### **FEATURES**

- Optimized for 5V Gate Drive
- Ultralow Q<sub>q</sub> and Q<sub>qd</sub>
- · Low Thermal Resistance
- · Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- · Halogen Free
- SON 5-mm × 6-mm Plastic Package

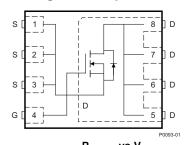
## **APPLICATIONS**

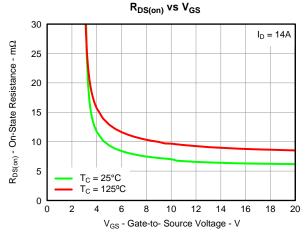
- · Notebook Point of Load
- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems

#### DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications, and optimized for 5V gate drive applications.

Figure 1. Top View





#### PRODUCT SUMMARY

$V_{DS}$	Drain to Source Voltage 30				
$Q_g$	Gate Charge Total (4.5V)	3.6	nC		
$Q_{gd}$	Gate Charge Gate to Drain	1.1	nC		
Б	Drain to Source On Resistance	$V_{GS} = 4.5V$	10	mΩ	
R <sub>DS(on)</sub>	Diam to Source On Resistance	V <sub>GS</sub> = 10V 6.7		mΩ	
$V_{GS(th)}$	Threshold Voltage	1.6	V		

#### ORDERING INFORMATION

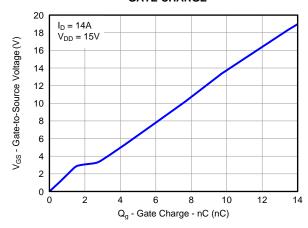
Device	Package	Media	Qty	Ship
CSD17522Q5A	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

#### **ABSOLUTE MAXIMUM RATINGS**

T <sub>A</sub> = 2	5°C unless otherwise stated	VALUE	UNIT					
$V_{DS}$	Drain to Source Voltage	30	٧					
$V_{GS}$	Gate to Source Voltage	±20	V					
	Continuous Drain Current, T <sub>C</sub> = 25°C	87	Α					
I <sub>D</sub>	Continuous Drain Current <sup>(1)</sup>	16	Α					
$I_{DM}$	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	104	Α					
$P_D$	Power Dissipation <sup>(1)</sup>	3	W					
$T_J$ , $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to 150	°C					
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D = 33A$ , $L = 0.1 mH$ , $R_G = 25\Omega$	54	mJ					

- (1) Typical  $R_{\theta JA}=41^{\circ}\text{C/W}$  on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.
- (2) Pulse duration ≤300µs, duty cycle ≤2%

#### **GATE CHARGE**



A

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## **ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static C	haracteristics		·			
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	30			V
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 24V			1	μΑ
$I_{GSS}$	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.1	1.6	2.0	V
D	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 14A$		10	12.4	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 14A$		6.7	8.1	mΩ
9 <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 15V, I <sub>D</sub> = 14A		37		S
Dynamic	Characteristics					
C <sub>iss</sub>	Input Capacitance			580	695	pF
C <sub>oss</sub>	Output Capacitance	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		390	470	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			35	44	pF
$R_G$	Series Gate Resistance			4.7		Ω
Qg	Gate Charge Total (4.5V)			3.6	4.3	nC
$Q_{gd}$	Gate Charge Gate to Drain	V 45V L 44A		1.1		nC
$Q_{gs}$	Gate Charge Gate to Source	$V_{DS} = 15V, I_{D} = 14A$		1.6		nC
Q <sub>g(th)</sub>	Gate Charge at Vth			0.9		nC
Q <sub>oss</sub>	Output Charge	V <sub>DS</sub> = 13V, V <sub>GS</sub> = 0V		8.6		nC
t <sub>d(on)</sub>	Turn On Delay Time			6.7		ns
t <sub>r</sub>	Rise Time	$V_{DS} = 15V, V_{GS} = 4.5V,$		12		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$I_{DS} = 14A, R_G = 2\Omega$		10.5		ns
t <sub>f</sub>	Fall Time			3.7		ns
Diode C	haracteristics				'	
$V_{SD}$	Diode Forward Voltage	$I_{SD} = 14A$ , $V_{GS} = 0V$		0.85	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	V <sub>DD</sub> = 13V, I <sub>F</sub> = 14A,		19.6		nC
t <sub>rr</sub>	Reverse Recovery Time	di/dt = 300A/µs		17.8		ns

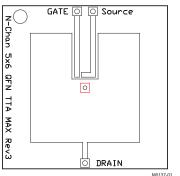
## THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

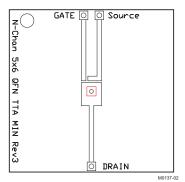
	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case <sup>(1)</sup>			1.8	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient <sup>(1)(2)</sup>			51	°C/W

 $R_{\theta JC}$  is determined with the device mounted on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB.  $R_{\theta JC}$  is specified by design, whereas  $R_{\theta JA}$  is determined by the user's board design. Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.





Max  $R_{\theta JA} = 51^{\circ} C/W$  when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max  $R_{\theta JA} = 125^{\circ} C/W$  when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

## TYPICAL MOSFET CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

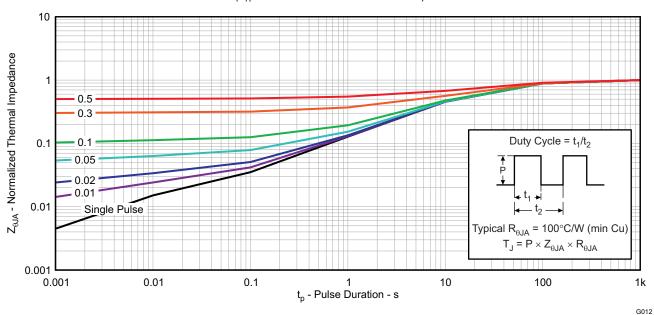


Figure 2. Transient Thermal Impedance



## TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

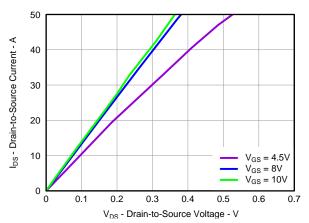


Figure 3. Saturation Characteristics

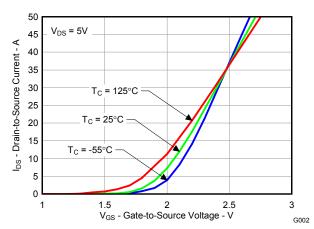


Figure 4. Transfer Characteristics

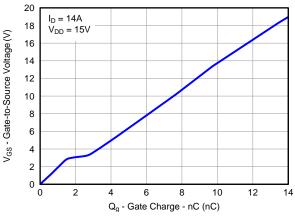


Figure 5. Gate Charge

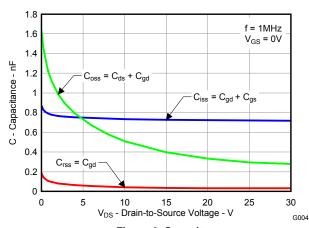


Figure 6. Capacitance

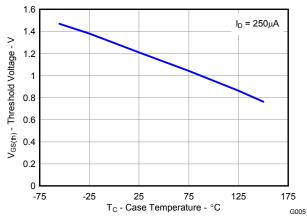


Figure 7. Threshold Voltage vs. Temperature

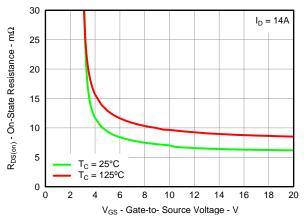


Figure 8. On-State Resistance vs. Gate-to-Source Voltage



## **TYPICAL MOSFET CHARACTERISTICS (continued)**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

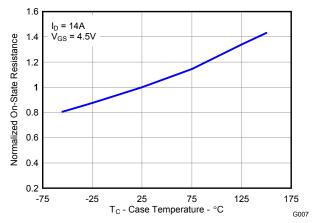


Figure 9. Normalized On-State Resistance vs. Temperature

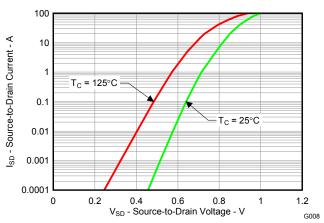


Figure 10. Typical Diode Forward Voltage

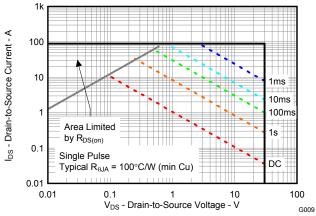


Figure 11. Maximum Safe Operating Area

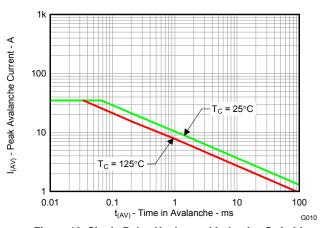


Figure 12. Single Pulse Unclamped Inductive Switching

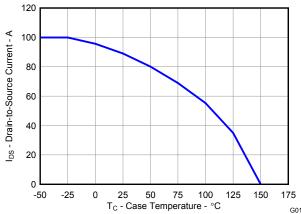
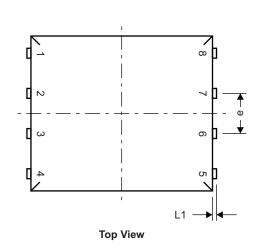


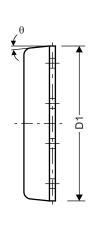
Figure 13. Maximum Drain Current vs. Temperature



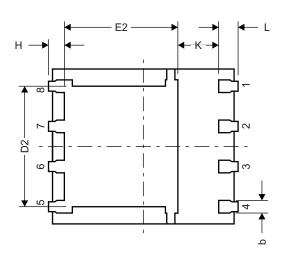
## **MECHANICAL DATA**

## **Q5A Package Dimensions**





Side View



Front View

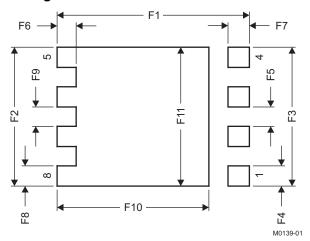
**Bottom View** 

M0135-01

DIM	MILLIMETERS					
DIM	MIN	NOM	MAX			
А	A 0.90		1.10			
b	0.33	0.41	0.51			
С	0.20	0.25	0.34			
D1	4.80	4.90	5.00			
D2	3.61	3.81	4.02			
Е	5.90	6.00	6.10			
E1	5.70	5.75	5.80			
E2	3.38	3.58	3.78			
е	1.17	1.27	1.37			
Н	0.41	0.56	0.71			
K	1.10					
L	0.51	0.61	0.71			
L1	0.06	0.13	0.20			
θ	0°		12°			



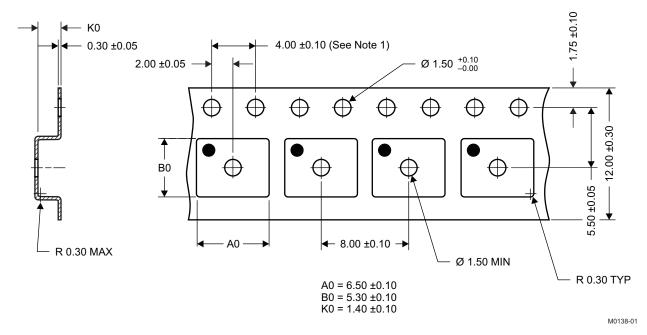
Figure 14. Recommended PCB Pattern



DIM	MILLIM	IETERS	INCHES		
DIN	MIN	MAX	MIN	MAX	
F1	6.205	6.305	0.244	0.248	
F2	4.46	4.56	0.176	0.18	
F3	4.46	4.56	0.176	0.18	
F4	0.65	0.7	0.026	0.028	
F5	0.62	0.67	0.024	0.026	
F6	0.63	0.68	0.025	0.027	
F7	0.7	0.8	0.028	0.031	
F8	0.65	0.7	0.026	0.028	
F9	0.62	0.67	0.024	0.026	
F10	4.9	5	0.193	0.197	
F11	4.46	4.56	0.176	0.18	

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

## **Q5A Tape and Reel Information**



#### Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket



## **REVISION HISTORY**

Cł	hanges from Original (June 2011) to Revision A Page					
•	Changed V <sub>GS</sub> From: +20 / –12V To: ±20V in the Abs Max Ratings table	1				
•	Changed $I_{GSS}$ the Test Conditions From: $V_{DS} = 0V$ , $V_{GS} = \pm 20/-12V$ To: $V_{DS} = 0V$ , $V_{GS} = \pm 20V$	2				

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#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	<b>RoHS</b> (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
CSD17522Q5A	Active	Production	VSONP (DQJ)   8	2500   LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD17522
CSD17522Q5A.B	Active	Production	VSONP (DQJ)   8	2500   LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD17522

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

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